

**Silicon NPN Power Transistors**

**2SC4793**

**DESCRIPTION**

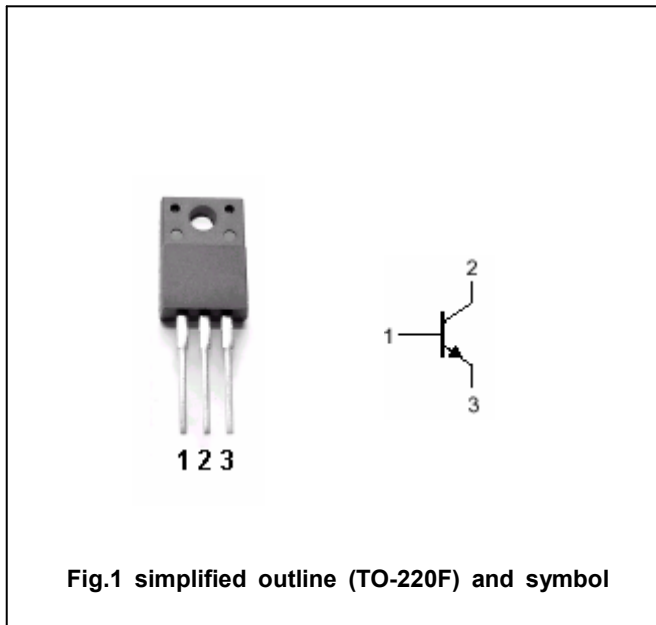
- With TO-220F package
- Complement to type 2SA1837
- High transition frequency

**APPLICATIONS**

- Power amplifier applications
- Driver stage amplifier applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



**Absolute maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	230	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	230	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		1	A
I <sub>B</sub>	Base current		0.1	A
P <sub>C</sub>	Collector dissipation	T <sub>C</sub> =25°C	20	W
		T <sub>a</sub> =25°C	2.0	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## 2SC4793

## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA ; I <sub>B</sub> =0	230			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =0.5A I <sub>B</sub> =50mA			1.5	V
V <sub>BE</sub>	Base-emitter voltage	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =5V			1.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =230V; I <sub>E</sub> =0			1.0	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			1.0	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =5V	100		320	
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =10V;f=1MHz		20		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =10V		100		MHz



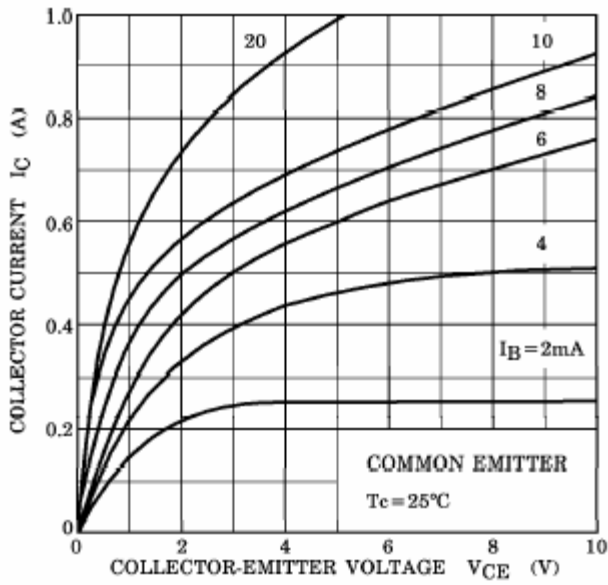


Fig.3 Static Characteristic

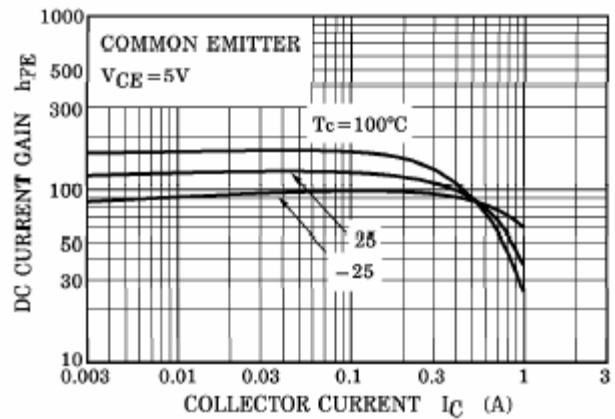


Fig.4 DC current Gain

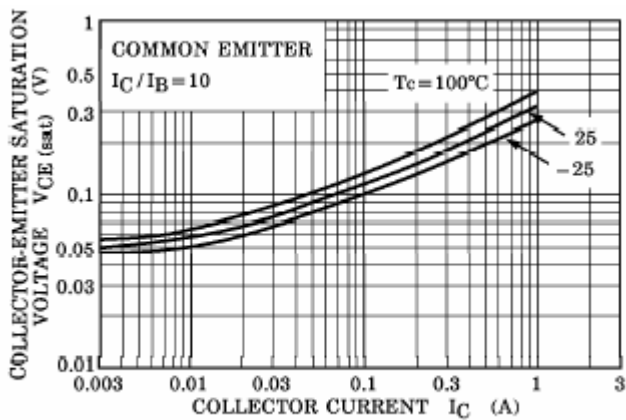


Fig.5 Collector-Emitter Saturation Voltage

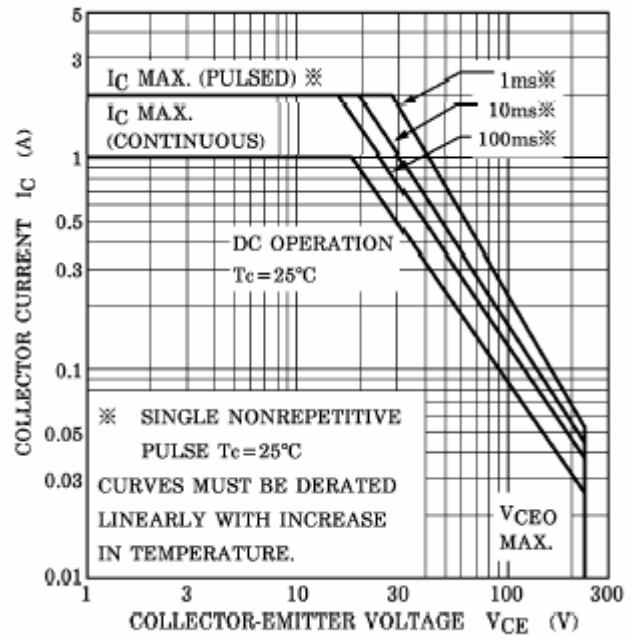


Fig.6 Safe Operating Area